-100V P-Channel Power MOSFET

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

■Low $R_{DS(ON)}$ to minimize conductive loss

■Low Gate Charge for fast switching

■Low Thermal resistance

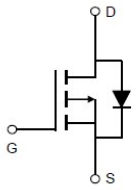
•Application

■BLDC Motor driver

■DC-DC

■Load switch

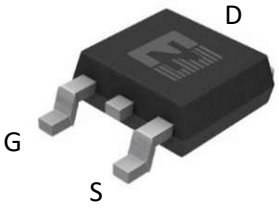
• Product Summary



V_{DS}= -100V

$R_{DS(ON)}$ = 40mΩ

I_D= -29A



TO-252

RoHS

REACH COMPLIANT

HF

•Ordering Information:

Part NO.	ZM350P10D
Marking	ZM350P10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

•Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		-100	V
Gate-Source Voltage	V_{GS}		±20	V
Continuous Drain Current	I_D	T_C=25℃	-29	A
	I_D	T_C=75℃	-24	A
	I_D	T_C=100℃	-21	A
Pulsed Drain Current	I_{DM}	Pulsed; t_p ≤ 10 μs; T_{mb} = 25 °C;	-116	A
Total Power Dissipation	P_D	T_C=25℃	100	W
Total Power Dissipation	P_D	T_A=25℃	2.4	W
Operating Junction Temperature	T_J		-55 to +175	℃
Storage Temperature	T_{STG}		-55 to +175	℃
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, V_{GS}=-10V, Rg=25Ω,	110	mJ
		L=0.5mH, V_{GS}=-10V, Rg=25Ω,	231	mJ
ESD Level (HBM)	CLASS 2			

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	1.5	°C/W
Thermal resistance, junction-ambient①	R_{thJA}		-	62	°C/W
Soldering temperature	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =-250uA	-100			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =-250uA	-1.3	-1.8	-2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}= -100V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} = 0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D= -15A		40	56	mΩ
		V_{GS}=-4.5V, I_D= -8A		52	70	mΩ
Forward Transconductance	g_{FS}	V_{DS} =-5V, I_{SD} = -10A		20		s
Diode Forward Voltage	V_{FSD}	V_{GS} =0V, I_{SD} = -15A			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V_{DS}=-25V	-	4500	-	pF
Output capacitance	Coss		-	398	-	
Reverse transfer capacitance	Crss		-	157	-	
Gate Risistance	Rg	f = 1MHz	-	4		Ω
Total gate charge	Qg	V_{DD} = -15V, I_D = -15A, V_{GS} = -10V	-	124	-	nC
	Qg(-4.5v)		-	61	-	
Gate - Source charge	Qgs		-	20	-	
Gate - Drain charge	Qgd		-	29	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=-10V,V_{DS}=-15V, R_G =3.3Ω, I_D =-10A	-	26	-	ns
Turn-ON Rise time	t_r		-	89	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	96	-	ns
Turn-Off Fall time	t_f		-	67	-	ns
Reverse Recovery Time	t_{RR}	V_{DD}=-20V, dI_S/dt = 100A/us, I_S=-20A	-	205	-	ns
Reverse Recovery Charge	Q_{RR}		-	467	-	nC

Fig.1 Gate-Charge Characteristics

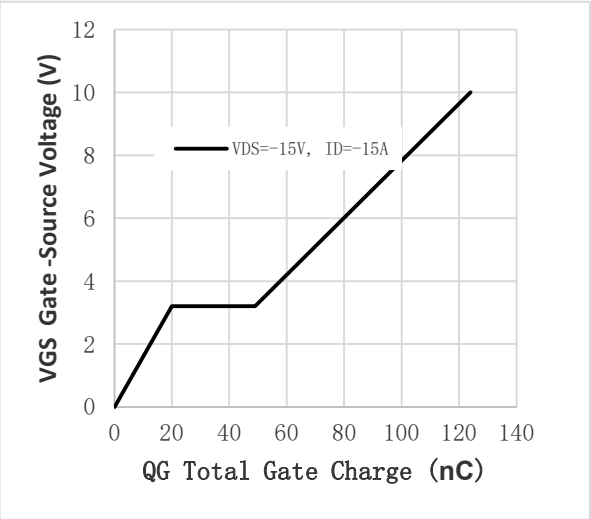


Fig.2 Capacitance Characteristics

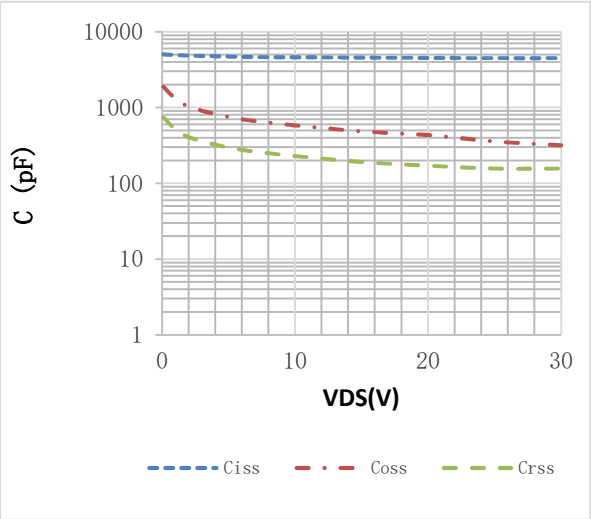


Fig.3 Power Dissipation

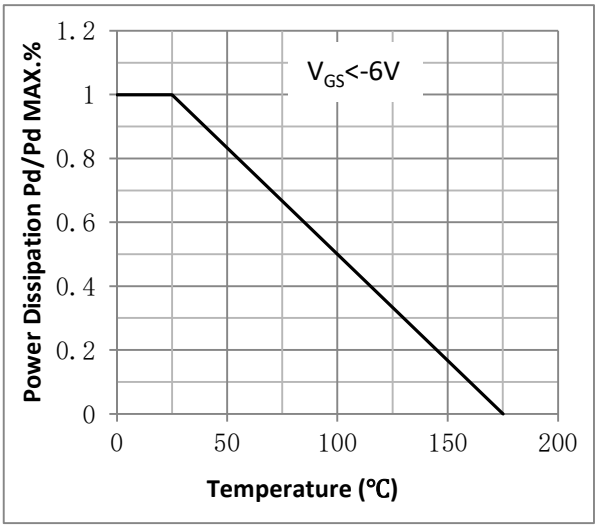


Fig.4 Typical output Characteristics

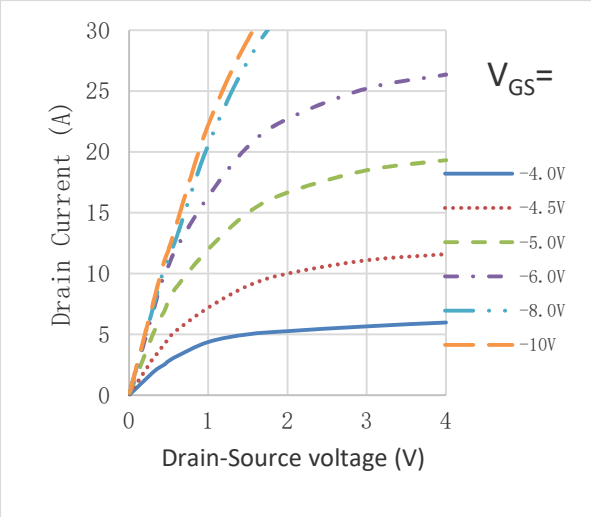


Fig.5 Threshold Voltage V.S Junction Temperature

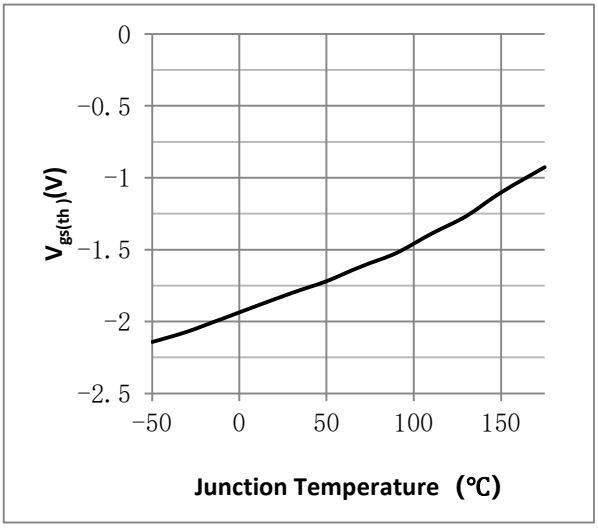


Fig.6 Resistance V.S Drain Current

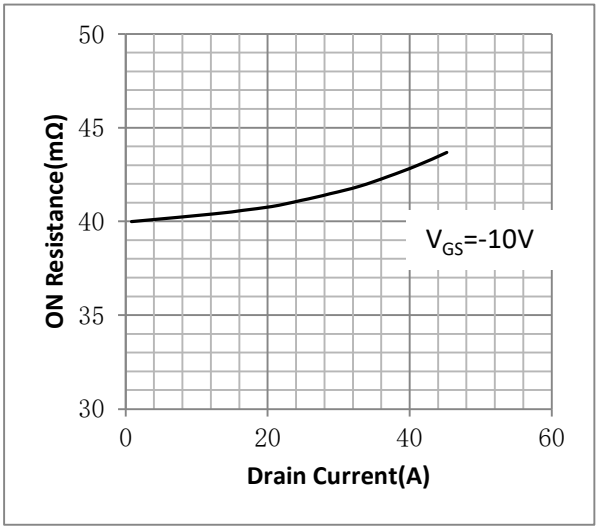


Fig.7 On-Resistance VS Gate Source Voltage

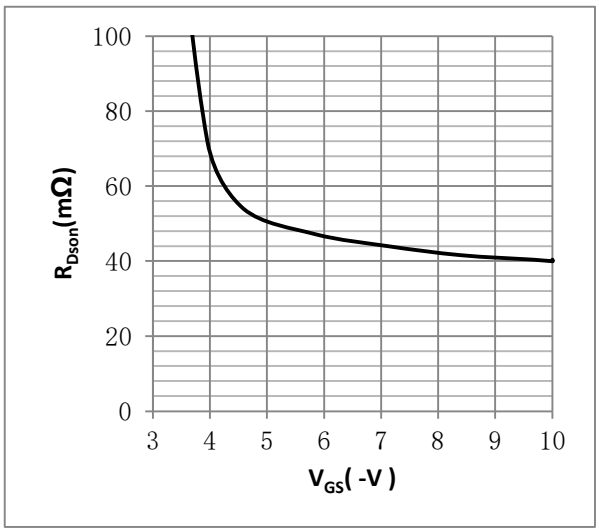


Fig.8 On-Resistance V.S Junction Temperature

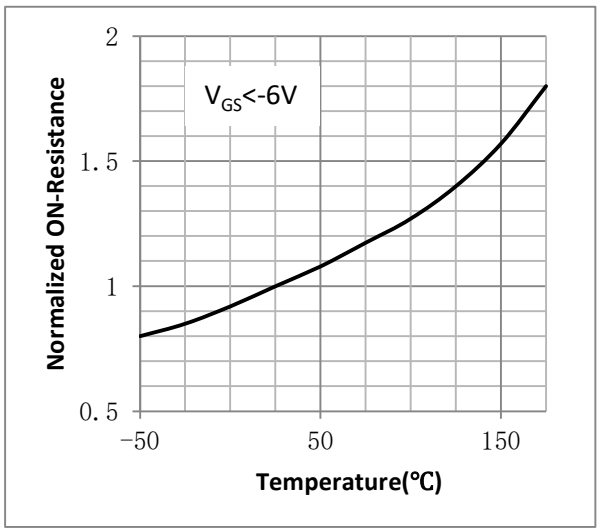


Figure 9. Diode Forward Voltage vs. Current

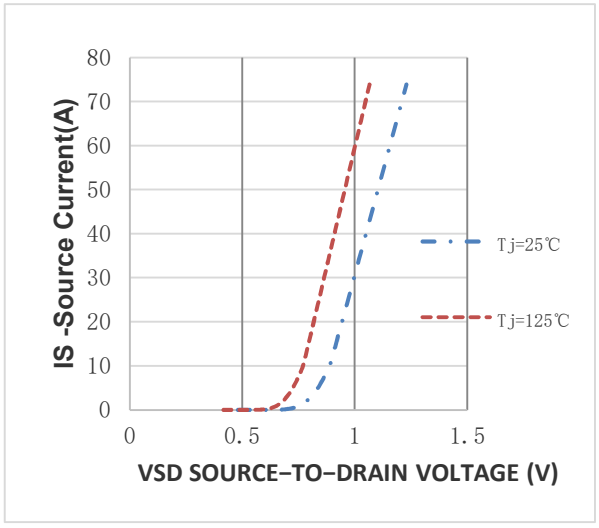


Figure 10. Transfer Characteristics

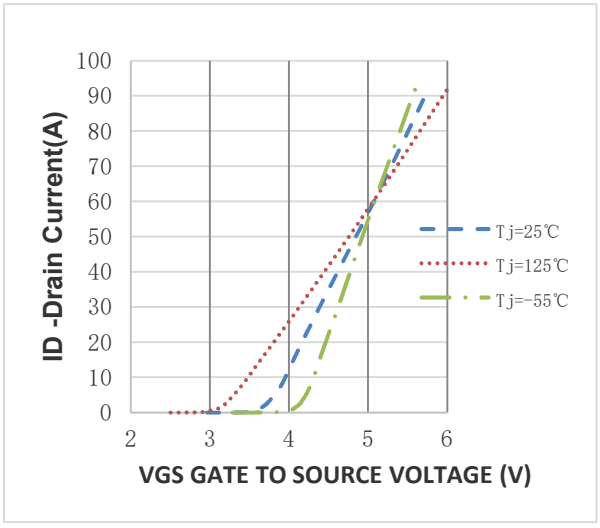


Fig.11 Safe Operating Area

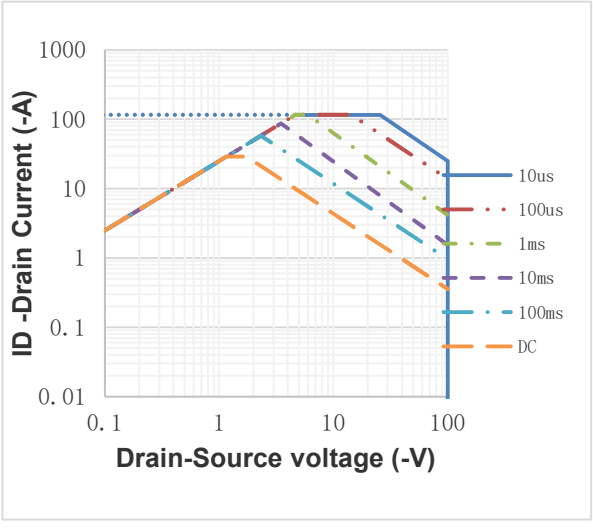
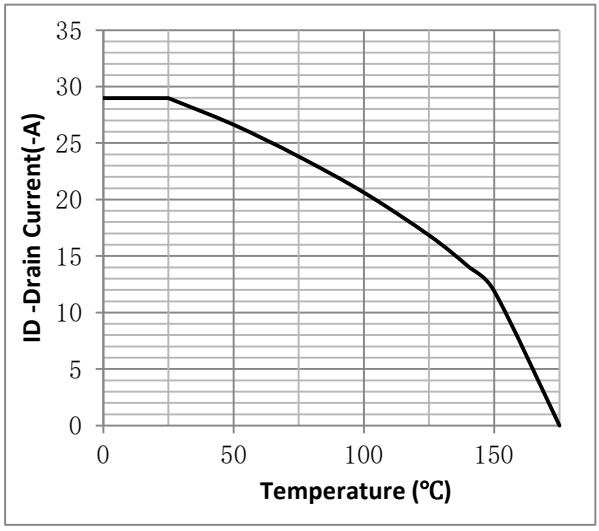
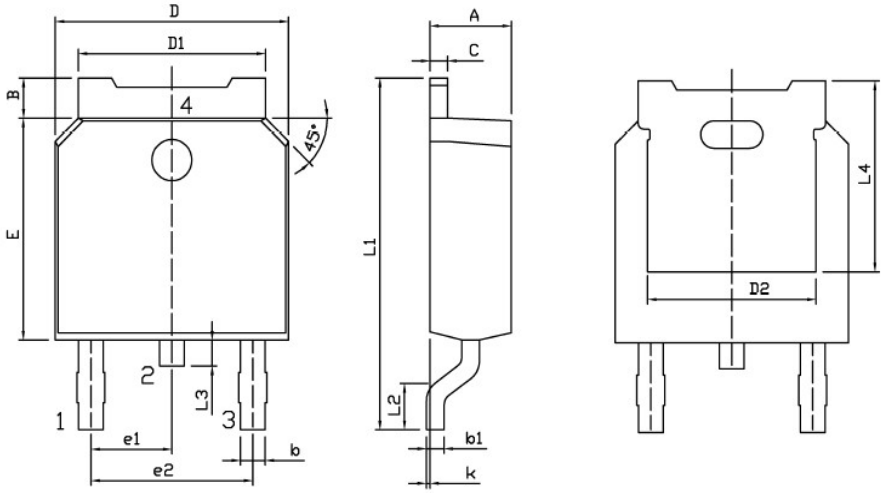


Fig.12 ID vs. Case Temperature②

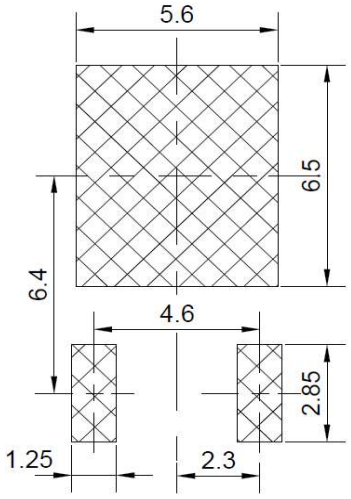


●TO-252 Package Outline



Dimensions In Millimeters					
Symbol	MIN	MAX	Symbol	MIN	MAX
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	L4	5.05	
D2	4.85		k	0.00	0.10

Land Pattern
(Only for Reference)



Note:

① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

②Practically the current will be limited by PCB, thermal design and operating temperature. VGS=10V.

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Revision History

Version	Date	Change
A	2021.12.3	NEW
B	2022.9.7	1.Add Reach,HF figure
C	2024.5.20	related curve
D	2025.11.14	Update POD